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DEC 05 2006

Application Serial Number 10/562,293  
Response to Office Action  
Dated September 6, 2006

1. Amendments to the Claims:

A listing of the entire set of pending claims (including amendments to the claims, if any) is submitted herewith per 37 CFR 1.121. This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1.-15. (CANCELLED).

16. (PREVIOUSLY PRESENTED) A TFT comprising a substrate a gate overlying the substrate and having side edges inclined towards one another, a channel region overlying the gate and source and drain regions overlying said side edges respectively, wherein the gate has been formed on the substrate by an etching process that involved formation of a tip in an apex region between the side edges of a radius of a few nanometres.

17. (ORIGINAL) A TFT according to claim 16 wherein the tip (13) was removed before the channel region was applied.

18. (PREVIOUSLY PRESENTED) A TFT according to claim 16 wherein the gate is overlaid by a layer of insulating material, the channel region overlies the insulating material, a layer of doped semiconductor material overlies the channel region, and a layer of conductive material from which said source and drain regions have been formed,

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overlies the doped semiconductor material.

19. (PREVIOUSLY PRESENTED) A TFT according to claim 16 wherein the channel region (6) comprises intrinsic amorphous silicon.

20. (ORIGINAL) A TFT according to claim 18 wherein the insulating layer comprises (5) silicon nitride.

21. (ORIGINAL) A TFT according to claim 18 wherein the doped semiconductor material (7) comprises n doped silicon.